

## ABSTRACT OF THE DISCLOSURE

There provided an electrostatic discharge protection circuit for preventing a damage to a transistor due to an ESD surge. In the protection circuit, a first and a second signal line serving as a source or a drain of a transistor Tr1 are connected to a first and a second power source terminal, respectively. A first diode has an anode connected to the first signal line and a cathode connected to a back gate of the transistor and a cathode of a second diode. The second diode has an anode connected to the second signal line 2. Thus, the source and drain of the transistor Tr1 are switched to each other in accordance with an ESD surge voltage generated in the first and the second signal line. Therefore, an ESD surge current runs through a source-drain path without producing a parasitic action in a well tap of the source and the drain, thereby preventing a damage to the transistor Tr1.